

Data sheet acquired from Harris Semiconductor SCHS051A – Revised March 2002

CD4066B Types

CMOS Quad Bilateral Switch

For Transmission or Multiplexing of Analog or **Digital Signals**

High-Voltage Types (20-Volt Rating)

■ CD4066B is a quad bilateral switch intended for the transmission or multiplexing of analog or digital signals. It is pin-forpin compatible with RCA-CD4016B, but exhibits a much lower on-state resistance. In addition, the on-state resistance is relatively constant over the full input-signal range.

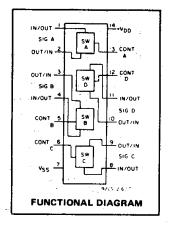
The CD4066B consists of four independent bilateral switches. A single control signal is required per switch. Both the p and the n device in a given switch are biased on or off simultaneously by the control signal. As shown in Fig.1, the well of the n-channel device on each switch is either tied to the input when the switch is on or to VSS when the switch is off. This configuration eliminates the variation of the switch-transistor threshold voltage with input signal, and thus keeps the on-state resistance low over the full operating-signal range.

The advantages over single-channel switches include peak input-signal voltage swings equal to the full supply voltage, and more constant on-state impedance over the input-signal range. For sample-and-hold applications, however, the CD4016B is recommended.

The CD4066B is available in 14-lead ceramic dual-in-line packages (D and F suffixes), 14-lead plastic dual-in-line packages (E suffix), 14-lead small-outline package (NSR suffix), and in chip form (H suffix).

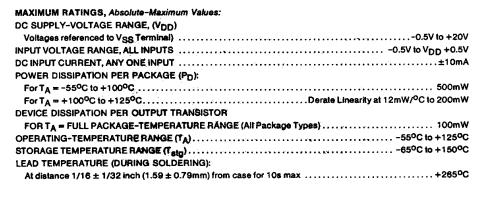
Features:

- 15-V digital or ±7.5-V peak-to-peak switching
- 125Ω typical on-state resistance for 15-V operation
- lacktriangle Switch on-state resistance matched to within 5 Ω over 15-V signal-input range
- On-state resistance flat over full peak-to-peak signal
- High on/off output-voltage ratio: 80 dB typ. @ $f_{is} = 10 \text{ kHz}, R_L = 1 \text{ k}\Omega$
- High degree of linearity: <0.5% distortion typ. @ f_{is} = 1 kHz, V_{is} = 5 Vp-p, V_{DD} - $V_{SS} \ge 10 \text{ V, R}_L = 10 \text{ k}\Omega$
- Extremely low off-state switch leakage resulting in very low offset current and high effective off-state resistance: 10 pA typ. @ VDD - VSS = 10 V, TA = 25°C
- Extremely high control input impedance (control circuit isolated from signal circuit): $10^{12} \Omega$ typ.
- Low crosstalk between switches: -50 dB typ. @ f_{is} = 8 MHz, R_L = 1 $k\Omega$
- Matched control-input to signal-output capacitance: Reduces output signal transients
- Frequency response, switch on = 40 MHz (tvp.)
- 100% tested for quiescent current at 20 V
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13B,"Standard Specifications for Description of "B" Series CMOS Devices"



Applications:

- Analog signal switching/multiplexing Signal gating Modulator Squelch control Demodulator Commutating switch Chopper
- Digital signal switching/Multiplexing
- Transmission-gate logic implementation
- Analog-to-digital & digital-to-analog conversion
- Digital control of frequency, impedance, phase, and analog-signal gain



RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	1141170		
CHARACTERISTIC	Min.	Max.	UNITS	
Supply-Voltage Range (For TA = Full Package-				
Temperature Range)	3	18	V	

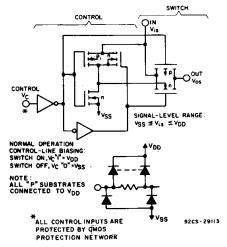


Fig. 1 - Schematic diagram of 1 of 4 identical switches and its associated control circuitry.

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ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	TEST CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)					U N I T S	
								+2	5]
		(Ÿ)	(V)	-55	-40	+85	+125	Тур.	Max.	
		0,5	5	0.25	0.25	7.5	7.5	0.01	0.25	_
Quiescent Device		0,10	10	0.5	0.5	15	15	0.01	0.5	L _A
Current, I _{DD}		0,15	15	1	1.	30	30	0.01	1	
· · · · · · · · · · · · · · · · · · ·	. 31	0,20	20	- 5	5	150	150	0.02	5	
Signal Inputs (V _{is}) and Output (V _{os})		,							
	V _C = V _{DD}									
On-State Resistance, ron	R _L = 10 kΩ returned		5	800	850	1200	1200	470	1050	
Max.	to V _{DD} – V _{SS}		<u> </u>	1	-			-		
IVIGA.	2 V: = V== to V==		10	310	330	500	550		400	Ω
A On State	Vis = VSS to VDD		15	200	210	300	320	125	240	
∆On-State Resistance			5		-		_	15	<u> </u>	
Between Any	$R_L = 10 k\Omega$, $V_C = V_{DD}$		10			_	- '	10		Ω
2 Switches, Δr_{on}				_	_	_	- :	5		
Total Harmonic Distortion, THD	$V_C = V_{DD} = 5 \text{ V}, V_{SS} = -$ = 5V (Sine wave centered R _L =10 k Ω , f _{is} =1 kHz sin	V)		_	-		0.4	-	%	
-3dB Cutoff Frequency (Switch on)	$V_{C}=V_{DD}=5V$, $V_{SS}=-5V$, $V_{is(p-p)}=5V$ (Sine wave centered on $0V$ R _L = 1 k Ω),			-,				40		мн
-50dB Feed- through Frequency (Switch off)	$V_{C}=V_{SS}=-5V$, $V_{is(p-p)}=5V$ Sine wave centerd on $0V$ $R_{L}=1 k\Omega$			1	· -	_	-	1	-	мн
Input/Output Leakage Current (Switch off) I _{is} Max.	V _C = 0 V V _{is} = 18 V; V _{os} = 0 V, V _{is} = 0V; V _{os} = 18 V		18	±0.1	±0.1	±1	±1	±10 ⁻⁵	±0.1	μΑ
-50 dB Crosstalk Frequency	$V_{C}(A) = V_{DD} = +5 \text{ V. } V_{C}(B) = V_{SS} = -5 \text{ V. } V_{is}(A) = 5 V_{p-p}, 50 \Omega \text{ source} $ R _L = 1 k Ω		:	_	1 .	1	1	8	1	МН
Propagation	RL = 200 kΩ		5		_		_	20	40	
Delay (Signal	$V_C = V_{DD}$, $V_{SS} = GND$, $C_L = 50 pF$ $V_{is} = 10 V$ (Square	i = V _{DD} , V _{SS} = 10, C _L = 50 pF 10			_		-	10	20	ns
Input to Signal Output) t _{pd}	$V_{is} = 10 \text{ V (Square}$ wave centered on 5 V t_r , $t_f = 20 \text{ ns}$			-		-		7	15	
Capacitance: Input, C _{is}	V _{DD} = +5 V			_	_	_	_	8	_	
Output, Cos	V _C = V _{SS} = -5 V			-	-	-	-	8		рF
Feedthrough, C _{ios}		_	-	_	-	0.5	_			

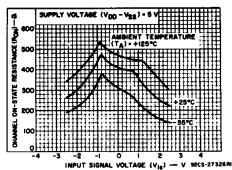


Fig. 2— Typical on-state resistance vs. input signal voltage (all types).

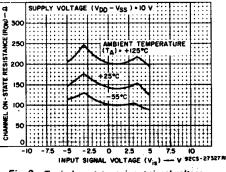


Fig. 3— Typical on-state vs. input signal voltage (all types).

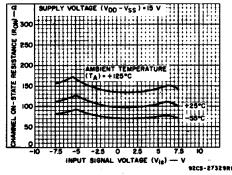


Fig. 4— Typical on-state resistance vs. input signal voltage (all types).

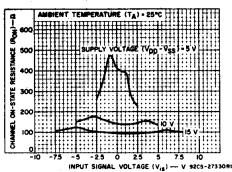
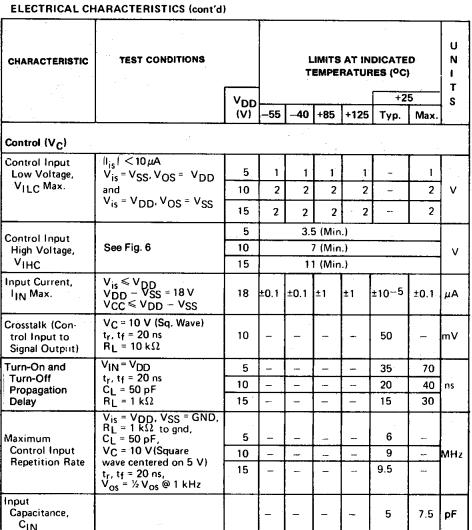


Fig. 5— on-state resistance vs. input signal voltage (all types).



CHARACTERISTIC	TEST CONDITIONS		LIMITS AT INDICATED TEMPERATURES (°C)					UNIT							
		V _{DD}	Ĺ				+2	5	s						
		(V)	-55	–40	+85	+125	Тур.	Max.							
Control (V _C)	.i														
Control Input Low Voltage,	$ I_{is} < 10 \mu\text{A}$ $V_{is} = V_{SS}, V_{OS} = V_{DD}$	5.	1	1	1	1	-	1							
VILC Max.	and	10	2	2	2	2	-	2	V	١.					
	$V_{is} = V_{DD}, V_{OS} = V_{SS}$	15	2	2	2	· 2		2]						
Control Input		. 5		3.	5 (Min	.)		<u> </u>							
High Voltage,	See Fig. 6	10		-	7 (Min	.)			V						
VIHC		15	11 (Min.)												
Input Current, I _{IN} Max.	V _{is} ≤ V _{DD} V _{DD} − V _{SS} = 18 V V _{CC} ≤ V _{DD} − V _{SS}	18	±0.1	±0.1	±1	±1	±10-5	±0.1	μΑ						
Crosstalk (Con- trol Input to Signal Output)	$V_C = 10 \text{ V (Sq. Wave)}$ t_r , $t_f = 20 \text{ ns}$ $R_L = 10 \text{ k}\Omega$	10	_	_	-	-	50	_	mV						
Turn-On and	V _{IN} = V _{DD}	5	_	-	-	-	35	70		ال					
Turn-Off Propagation	t _r , t _f = 20 ns C ₁ = 50 pF	10		-	-	-	20	40	ns						
Delay	R_ = 1 kΩ	15	-	_ "	- 1		15	30							
Maximum	$V_{is} = V_{DD}$, $V_{SS} = GND$, $R_L = 1 \text{ k}\Omega$ to gnd, $C_L = 50 \text{ pF}$,	5	_	_	_	_	6	_							
Control Input	V _C = 10 V(Square wave centered on 5 V) t _r , t _f = 20 ns, V _{OS} = ½ V _{OS} @ 1 kHz						10	_	_	-	-	9		MHz	l
Repetition Rate		15	_	-	-	+	9.5								
Input Capacitance, C _{IN}				_	-	1	5	7.5	рF						

	Switch Input Iis (mA)						Switch Output, V _{OS} (V)		
v _{DD}									
(V)	(V)	-55°C	-40°C	+25°C	+85°C	+125 ⁰ C	Min.	Max.	
5	0	0.64	0.61	0.51	0.42	0.36	-	0.4	
5	5	-0.64	-0.61	-0.51	-0.42	-0.36	4.6	–	
10	0	1.6	1.5	1.3	1.1	0.9	_	0.5	
10	10	-1.6	-1.5	-1.3	-1.1	-0.9	9.5	-	
15	0	4.2	4	3.4	2.8	2.4		1.5	
15	15	-4.2	-4	-3.4	-2.8	-2.4	13.5	_	

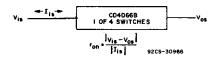


Fig. 6— Determination of $r_{\rm QD}$ as a test condition for control input high voltage (V_{IHC}) specification.

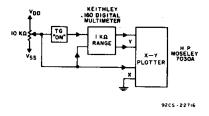


Fig. 7 - Channel on-state resistance measurement circuit.

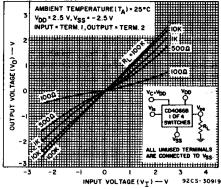


Fig. 8—Typical ON characteristics for 1 of 4 Channels.

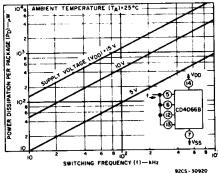


Fig. 9 - Power dissipation per package vs. switching frequency.

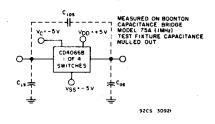


Fig. 10 - Capacitance test circuit.



Fig. 11 - Off-switch input or output leakage.

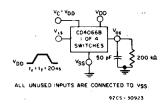


Fig. 12 — Propagation delay time signal input (V_{is}) to signal output (V_{OS}) .

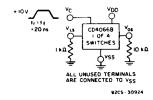


Fig. 13 - Crosstalk-control input to signal output.

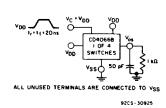


Fig. 14 — Propagation delay t_{PLH}, t_{PHL} controlsignal output. Delay is measured at V_{os} level of +10% from ground (turn-on) or on-state output level (turn-off).

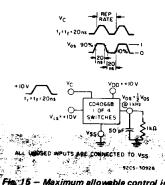


Fig. 15 — Maximum allowable control input repetition rate.

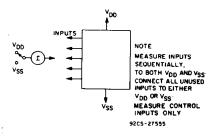


Fig. 16 - Input leakage current test circuit.

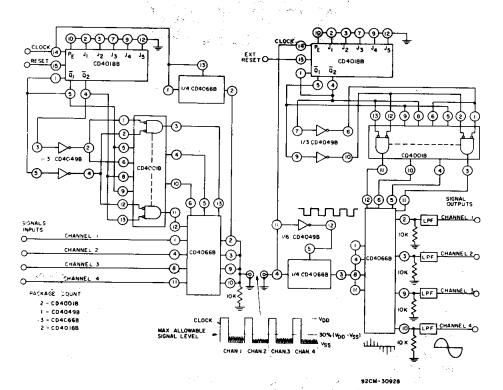


Fig. 17- 4-channel PAM multiplex system diagram.

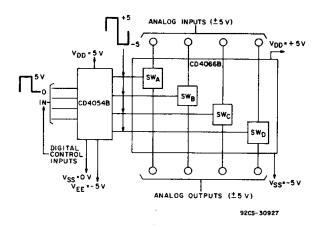
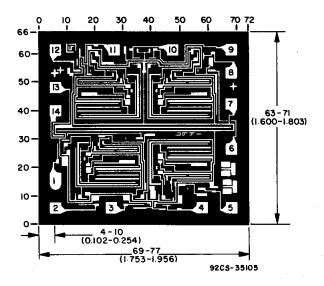


Fig. 18 — Bidirectional signal transmission via digital control logic.



CD4066BH CHIP DIMENSIONS AND PAD LAYOUT

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch) .

SPECIAL CONSIDERATIONS - CD4066B

- In applications that employ separate power sources to drive V_{DD} and the signal inputs, the V_{DD} current capability should exceed V_{DD}/R_L (R_L = effective external load of the four CD4066B bilateral switches). This provision avoids any permanent current flow or clamp action on the V_{DD} supply when power is applied or removed from the CD4066B.
- In certain applications, the external load-resistor current may include both VDD and signal-line components. To avoid drawing VDD current when switch current flows into terminals 1,4,8, or 11, the voltage drop across the bidirectional switch must not exceed 0.8 volts (calculated from RON values shown).

No Vpp current will flow through RL if the switch current flows into terminals 2,3,9, or 10.

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